

isc N-Channel MOSFET Transistor

IPU80R1K0CE

• FEATURES

- With TO-251(IPAK) packaging
- High speed switching
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

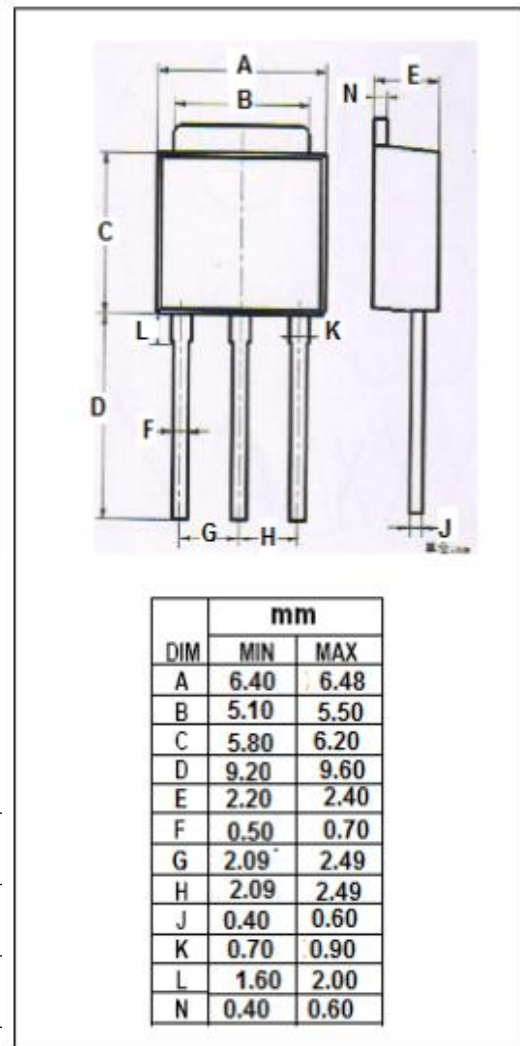
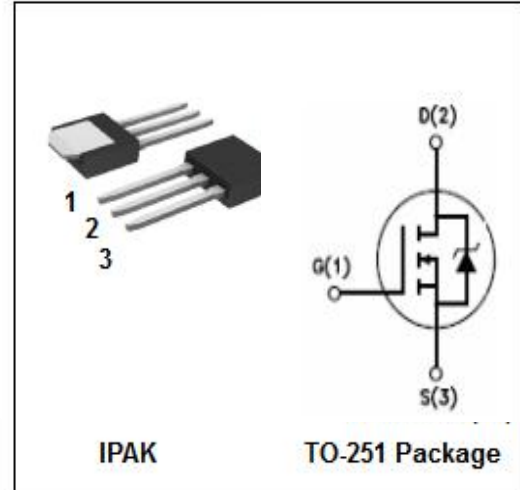
- Power supply
- DC-DC converters
- Motor control
- Switching applications

• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	800	V
V _{GSS}	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous	5.7	A
I _{DM}	Drain Current-Single Pulsed	18	A
P _D	Total Dissipation	83	W
T _j	Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature	-55~150	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	1.5	°C/W
R _{th(ch-a)}	Channel-to-ambient thermal resistance	62	°C/W



isc N-Channel MOSFET Transistor**IPU80R1K0CE****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=1.0mA$	800			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.25mA$	2.1		3.9	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=1A$		0.8	0.95	Ω
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=800V; V_{GS}=0V; T_J=25^{\circ}\text{C}$ $V_{DS}=800V; V_{GS}=0V; T_J=150^{\circ}\text{C}$			10 250	μA
V_{SDF}	Diode forward voltage	$I_{SD}=5.7A, V_{GS}=0V$			1.2	V